# 2:1 MIPI D-PHY (1.5 Gbps) 4 Data Lane Switch

# **FSA634**

#### Description

The FSA634 is configured as a 4 data lane, MIPI D-PHY switch. This single pole double throw (SPDT) switch is optimized for switching between two high speed or low power MIPI sources. The FSA634 is designed for the MIPI specification and allows connection to a CSI or DSI module.

#### **Features**

Switch Type: SPDT (10x)Signal Type: MIPI, D-PHY

• V<sub>CC</sub>: 1.65 to 4.5 V

ullet Input Signal: 0 V to  $V_{CC}$ 

 $\bullet$  R<sub>ON</sub>:

• 5 Ω Typical HS MIPI

• 5 Ω Typical LP MIPI

•  $\Delta R_{ON}$ : 0.1  $\Omega$  Typical

• R<sub>ON\_FLAT</sub>: 0.06 Ω Typical

• I<sub>CCZ</sub>: 0.5 μA Maximum

• I<sub>CC</sub>: 32 μA Maximum

• O<sub>IRR</sub>: -30 dB Typical

• Bandwidth: 1.9 GHz Typical

• Xtalk: -38 dB Typical

• CON: 4.3 pF Typical

• Skew: 3 ps Typical

#### **Applications**

• Cellular Phones, Smart Phones

• Tablets

• Laptops

• Displays



#### ON Semiconductor®

www.onsemi.com



(Bottom View)

WLCSP36, 2.06x2.06x0.432 CASE 567XU

#### **MARKING DIAGRAM**

VJKK XYZ

VJ = Specific Device Code

KK = Assembly Lot

X = Year

Y = Work Week

Z = Assembly Location

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

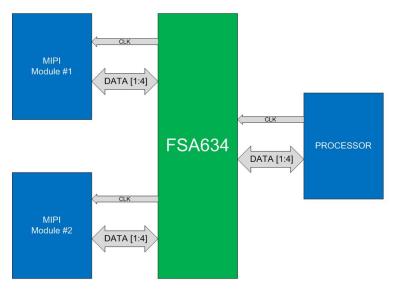
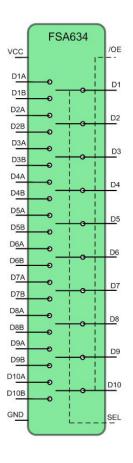


Figure 1. Typical Application

#### **PIN DESCRIPTIONS**



PIN NAME	DESCRIPT	ION	
Dn	Common	Data Path	j
DnA	Data Path	ı A	
DnB	Data Path	в	
/OE	Output Er	nable	
OF.	Control	SEL=0	Dn = DnA
SEL	Pin	SEL=1	Dn = DnB
VCC	Power	5.	
GND	Ground		
NC	No Conne	ect	

Figure 2. Analog Symbol

## **PIN DEFINITIONS**

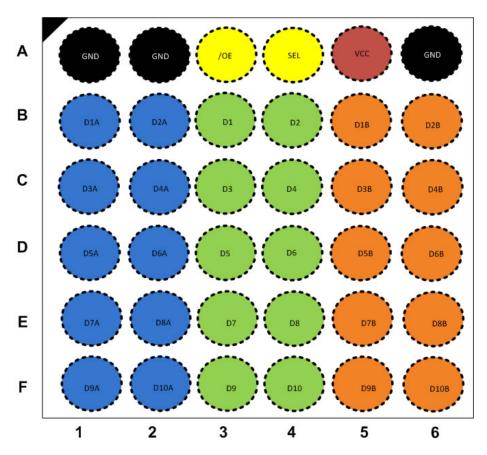


Figure 3. Top Through View

Table 1. BALL-TO-PIN MAPPINGS

Ball	Pin Name	Ball	Pin Name	Ball	Pin Name
A1	GND	C1	D3A	E1	D7A
A2	GND	C2	D4A	E2	D8A
А3	/OE	C3	D3	E3	D7
A4	SEL	C4	D4	E4	D8
A5	V <sub>CC</sub>	C5	D3B	E5	D7B
A6	GND	C6	D4B	E6	D8B
B1	D1A	D1	D5A	F1	D9A
B2	D2A	D2	D6A	F2	D10A
В3	D1	D3	D5	F3	D9
B4	D2	D4	D6	F4	D10
B5	D1B	D5	D5B	F5	D9B
B6	D2B	D6	D6B	F6	D10B

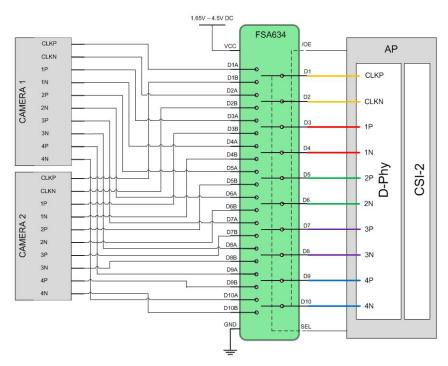


Figure 4. Suggested Configuration for 4 Lane D-PHY

#### **TRUTH TABLE**

SEL	/OE	Function
LOW	LOW	Dn = DnA
HIGH	LOW	Dn = DnB
X	HIGH	All Ports High Impedance

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	Supply Voltage	Supply Voltage			V
V <sub>CNTRL</sub>	DC Input Voltage (/OE, SEL) (Note 1)			V <sub>CC</sub>	V
$V_{SW}$	DC Switch I/O Voltage (Note 1,2)			V <sub>CC</sub>	V
I <sub>IK</sub>	DC Input Diode Current				mA
l <sub>OUT</sub>	DC Output Current			50	mA
T <sub>STG</sub>	Storage Temperature			+150	°C
ESD	Human Body Model, JEDEC: JESD22-A114 All Pins		3.5		kV
	Charged Device Model, JEDEC: JESD22-C101	Charged Device Model, JEDEC: JESD22-C101			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

2. V<sub>SW</sub> refers to analog data switch paths.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Supply Voltage		1.65	4.50	V
V <sub>CNTRL</sub>	Control Input Voltage (SEL, /OE) (Note 3)		0	V <sub>CC</sub>	V
$V_{SW}$	Switch I/O Voltage HS Mode		0	0.425	V
	(Dn, DAn, DBn)	LP Mode	0	1.3	V
T <sub>A</sub>	Operating Temperature		-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

3. The control inputs must be held HIGH or LOW; they must not float.

# **ELECTRICAL SPECIFICATION TABLE** Typical values are at $T_A = 25^{\circ}C$ , $V_{CC} = 3.3 \text{ V}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
ELECTRICAL PARA	METERS					
V <sub>IK</sub>	Clamp Diode Voltage	$I_{IN} = -18 \text{ mA}, V_{CC} = 1.8 \text{ V}$			-1.2	V
V <sub>IH</sub>	Input Voltage High	V <sub>CC</sub> = 1.65 V to 4.50 V	1.0			V
V <sub>IL</sub>	Input Voltage Low	V <sub>CC</sub> = 1.65 V to 4.50 V			0.4	V
I <sub>IN</sub>	Control Input Leakage (SEL,/OE)	$V_{SW} = 0 \text{ V to } V_{CC}, V_{CC} = 1.65 \text{ V to } 4.50 \text{ V}$	-500		500	nA
IN <sub>O(OFF)</sub> , IN <sub>C(OFF)</sub>	Off Leakage Current of Port Dn, DnA, DnB	Dn = 0.3 V to $V_{CC}$ – 0.3 V; DnA or DnB = Floating, 0.3 V, or $V_{CC}$ – 0.3 V; /OE = 0 V; $V_{CC}$ = 1.65 V to 4.5 V	-500		500	nA
I <sub>A(ON)</sub>	On Leakage Current of Common Ports (Dn)	$\begin{array}{l} \text{Dn} = 0.3 \text{ V to V}_{\text{CC}} - 0.3 \text{ V; DnA or DnB} = \\ \text{Floating, 0.3 V, or V}_{\text{CC}} - 0.3 \text{ V; /OE} = 0 \text{ V;} \\ \text{V}_{\text{CC}} = 1.65 \text{ V to 4.5 V} \end{array}$	-500		500	nA
I <sub>OFF</sub>	Power-Off Leakage Current	Dn, DnA or DnB; $V_{IN} = 0 \text{ V to } 4.5 \text{ V};$ $V_{CC} = 0 \text{ V}$	-500		500	nA
IOZ	Off-State Leakage	$0 \le Dn$ , $DnA$ , $DnB \le 3.6$ V, $/OE = High$ , $V_{CC} = 4.5$ V	-500		500	nA
R <sub>ON_MIPI_HS_1p8</sub>	Switch On Resistance for HS MIPI Applications	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 1.8$ V		5	12	Ω
R <sub>ON_MIPI_HS_2p5</sub>	(Note 5)	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 2.5$ V		5	9	Ω
R <sub>ON_MIPI_HS_3p6</sub>		$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 3.6$ V		5	9	Ω
R <sub>ON_MIPI_HS_4p5</sub>		$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC} = 4.5$ V		5	9	Ω
R <sub>ON_MIPI_LP_1p8</sub>	Switch On Resistance for LP MIPI Applications	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 1.8$ V		5	12	Ω
R <sub>ON_MIPI_LP_2p5</sub>	(Note 5)	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 2.5$ V		5	9	Ω
R <sub>ON_MIPI_LP_3p6</sub>	7	$I_{ON} = -10$ mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, $V_{CC} = 3.6$ V		5	9	Ω
R <sub>ON_MIPI_LP_4p5</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V V <sub>CC</sub> = 4.5 V		5	9	Ω

**ELECTRICAL SPECIFICATION TABLE** Typical values are at  $T_A = 25^{\circ}C$ ,  $V_{CC} = 3.3 \text{ V}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OC ELECTRICAL PARAM	IETERS					
ΔR <sub>ON_MIPI_HS_1p8</sub>	On Resistance Matching Between HS MIPI Chan-	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 1.8 V		0.10		Ω
$\Delta R_{ON\_MIPI\_HS\_2p5}$	nels	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 2.5 V		0.10		Ω
ΔR <sub>ON_MIPI_HS_3p6</sub>	]	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 3.6 V		0.10		Ω
ΔR <sub>ON_MIPI_HS_4p5</sub>	]	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 4.5 V		0.10		Ω
ΔR <sub>ON_MIPI_LP_1p8</sub>	On Resistance Matching Between LP MIPI Chan-	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 1.8 V		0.12		Ω
ΔR <sub>ON_MIPI_LP_2p5</sub>	nels	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 2.5 V		0.12		Ω
ΔR <sub>ON_MIPI_LP_3p6</sub>		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 3.6 V		0.12		Ω
$\Delta R_{ON\_MIPI\_LP\_4p5}$		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 4.5 V		0.12		Ω
R <sub>ON_FLAT_MIPI_HS_1p8</sub>	On Resistance Flatness for HS MIPI Signals	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 1.8 V		0.04		Ω
R <sub>ON_FLAT_MIPI_HS_2p5</sub>		$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 2.5 V		0.06		Ω
R <sub>ON_FLAT_MIPI_HS_3p6</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 3.6 V		0.06		Ω
R <sub>ON_FLAT_MIPI_HS_4p5</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, $V_{CC}$ = 4.5 V		0.06		Ω
R <sub>ON_FLAT_MIPI_LP_1p8</sub>	On Resistance Flatness for LP MIPI Signals	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 1.8 V		0.18		Ω
R <sub>ON_FLAT_MIPI_LP_2p5</sub>	1	$I_{ON}$ = -10 mA, /OE = 0 V, SEL = $V_{CC}$ or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, $V_{CC}$ = 2.5 V		0.28		Ω
R <sub>ON_FLAT_MIPI_LP_3p6</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V <sub>CC</sub> = 3.6 V		0.28		Ω
R <sub>ON_FLAT_MIPI_LP_4p5</sub>		I <sub>ON</sub> = -10 mA, /OE = 0 V, SEL = V <sub>CC</sub> or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V <sub>CC</sub> = 4.5 V		0.28		Ω
I <sub>CCZ</sub>	Quiescent Hi–Z Supply Current	$V_{IN} = 0 \text{ V or } V_{CC}, I_{OUT} = 0 \text{ A}, V_{CC} = 4.5 \text{ V}$			0.5	μΑ
Icc	Quiescent Supply Current	$V_{IN} = 0$ or $V_{CC}$ , $I_{OUT} = 0$ A, $V_{CC} = 2.5$ V to 4.5 V		16	32	μΑ
I <sub>CC_1p8</sub>	1	$V_{IN} = 0$ or $V_{CC}$ , $I_{OUT} = 0$ A, $V_{CC} = 1.8$ V		15	25	μΑ
I <sub>CCT_4p5</sub>	Increase in I <sub>CC</sub> Current	V <sub>SEL</sub> = 1.65 V, /OE = 1.65 V, V <sub>CC</sub> = 4.5 V			4	μΑ
I <sub>CCT_2p5</sub>	Per Control Voltage and V <sub>CC</sub>	V <sub>SEL</sub> = 1.65 V, /OE = 1.65 V, V <sub>CC</sub> = 2.5 V			0.1	μΑ
C ELECTRICAL PARAM						
t <sub>INIT</sub>	Initalization Time V <sub>CC</sub> to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V			100	μS
t <sub>INIT_1p8</sub>	7	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$			150	μS
t <sub>EN</sub>	Enable Turn-On Time, /OE to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V		120	200	ns
t <sub>EN_1p8</sub>	1	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$		250	500	ns
t <sub>DIS</sub>	Disable Turn-Off Time, /OE to Output	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 2.5 V to 4.5 V		25	50	ns
t <sub>DIS_1p8</sub>	1	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 1.2 V$ , $V_{CC} = 1.8 V$		50	90	ns

ELECTRICAL SPECIFICATION TABLE Typical values are at T<sub>A</sub> = 25°C, V<sub>CC</sub> = 3.3 V unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
LECTRICAL PAR	AMETERS			J.		<u></u>
t <sub>ON</sub>	Turn-On Time, SEL to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t <sub>ON_1p8</sub>		$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.8 V, SEL = H to L, SEL = L to H			300	ns
t <sub>OFF</sub>	Turn-Off Time SEL to Output	R <sub>L</sub> = 50 $\Omega$ , C <sub>L</sub> = 5 pF, V <sub>SW</sub> = 1.2 V, V <sub>CC</sub> = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t <sub>OFF_1p8</sub>		$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.8 V, SEL = H to L, SEL = L to H			300	
t <sub>BBM</sub>	Break-Before-Make Time	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, $V_{SW}$ = 1.2 V, $V_{CC}$ = 1.65 V to 4.5 V	10	50		ns
OIRR	Off Isolation for MIPI (Note 5)	$R_L = 50 \ \Omega, f = 750 \ MHz, /OE = V_{CC}, V_{SW} = -1 \ dBm \ (200 \ mV_{PP}), V_{CC} = 1.65 \ V \ to \ 4.5 \ V$		-30		dB
XTALK	Crosstalk for MIPI (Note 5)	$R_L = 50 \ \Omega, f = 750 \ MHz, V_{SW} = -1 \ dBm$ (200 mV <sub>PP</sub> ), $V_{CC} = 1.65 \ V$ to 4.5 V		-38		dB
BW	Bandwidth at -3dB (Note 5)	$R_L = 50 \Omega$ , $C_L = 0 pF$ , $V_{CC} = 3 V$		1.9		GHz
t <sub>SK(O)</sub>	Channel-to-Channel Sin- gle-Ended Skew (Note 5)	TDR-Based Method ( $V_{SW}$ = 0.2 $V_{PP}$ , $C_L$ = $C_{ON}$ ), $V_{CC}$ = 3.3 $V$		3	20	ps
<sup>t</sup> SK(P)	Skew of Opposite Transitions of the Same Output (Note 5)	TDR-Based Method ( $V_{SW}$ = 0.2 $V_{PP}$ , $C_L$ = $C_{ON}$ ), $V_{CC}$ = 3.3 $V$		3	20	ps
PACITANCE						
C <sub>IN</sub>	Control Pin Input Capacitance (Note 5)	V <sub>CC</sub> = 0 V, f = 1 MHz		2.7		pF
C <sub>ON</sub>	Out On Capacitance (Note 5)	V <sub>CC</sub> = 3.3 V, /OE = 0 V, f = 1 MHz		4.3		pF
C <sub>OFF</sub>	Out Off Capacitance (Note 5)	$V_{CC}$ and $/OE = 3.3 \text{ V, f} = 1 \text{ MHz}$		1.9		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Guarantee Levels:

- 4. Guaranteed by Design. Characterized on the ATE or Bench.
- 5. Guaranteed by Design and Characterization, not Production Tested.

The table below pertains to the Packaging information on the following page.

#### ORDERING INFORMATION

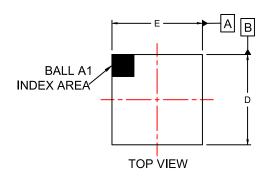
Part Number	Operating Temperature Range	Package	Top Mark
FSA634UCX	−40 to +85°C	36-Ball WLCSP, Non-JEDEC 2.06 x 2.06 mm, 0.35 mm Pitch	VJ

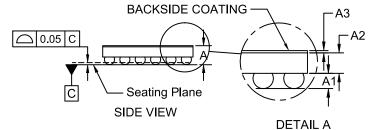


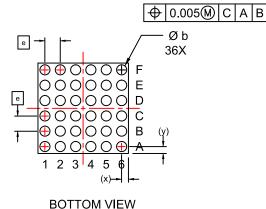
# WLCSP36 2.06x2.06x0.432

CASE 567XU ISSUE O

**DATE 26 APR 2019** 



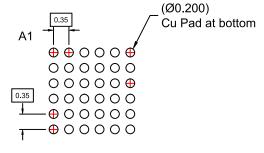




#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DATUM C APPLIES TO THE SPHERICAL CROWN OF THE SOLDER BALLS

	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
Α	0.391	0.432	0.473	
A1	0.154	0.174	0.194	
A2	0.215	0.233	0.251	
A3	0.022	0.025	0.028	
b	0.211	0.231	0.251	
D	2.03	2.06	2.09	
E	2.03	2.06	2.09	
е	0.35 BSC			
х	0.140	0.155	0.170	
у	0.140	0.155	0.170	



# RECOMMENDED MOUNTING FOOTPRINT\* (NSMD PAD TYPE)

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRIMD.

DOCUMENT NUMBER:	98AON06820H	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	WLCSP36 2.06x2.06x0.432		PAGE 1 OF 1		

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer p

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative